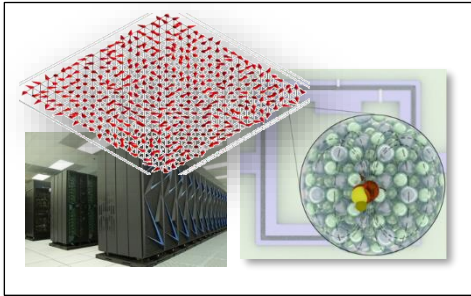


Simulating interactions between a qubit and a resonant two-level system bath

Yaniv J. Rosen, Yujin Cho, Dipti Jasrasaria, Keith G. Ray, Daniel M. Tennant, Vincenzo Lordi, and Jonathan L DuBois



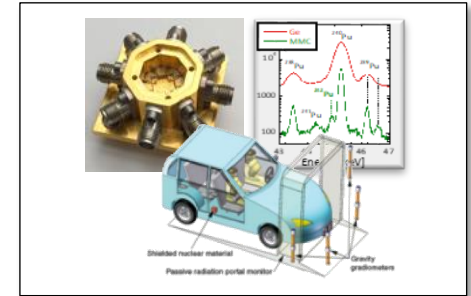
Testbed activities interface with a broad range of facilities and expertise at the lab



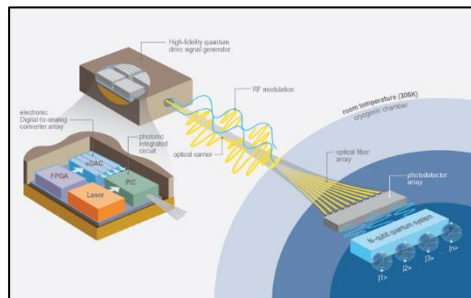
HPC & Computational
Materials Science



Design, fabrication,
characterization and control
of superconducting quantum
systems



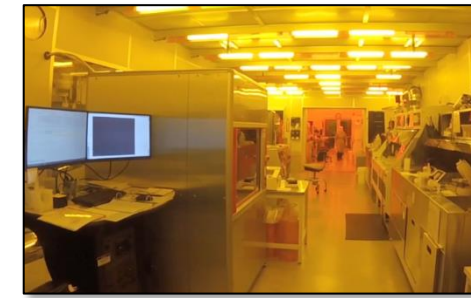
Sensing & Detection



Photon Science & Systems
Engineering



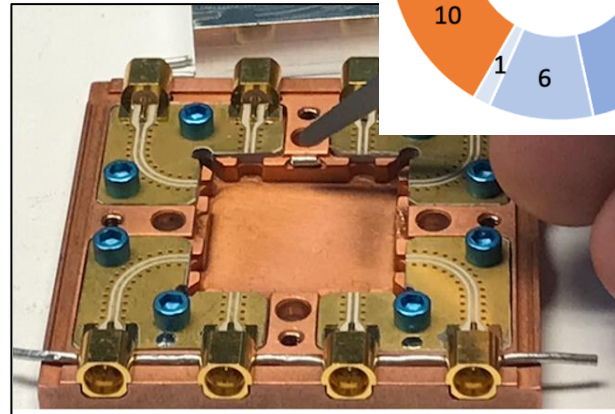
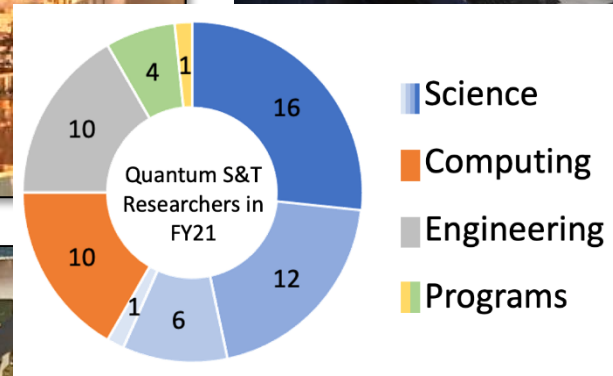
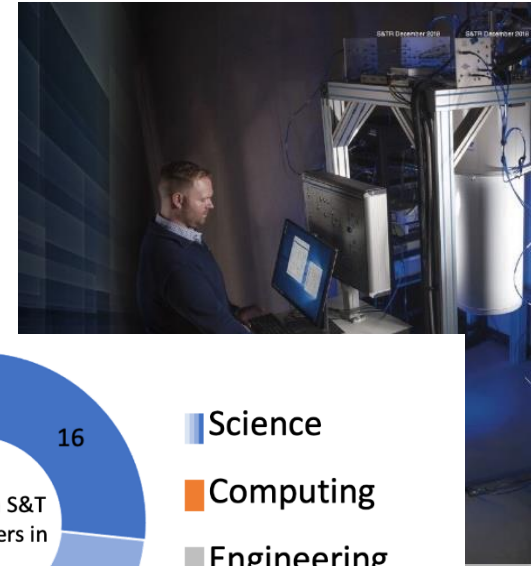
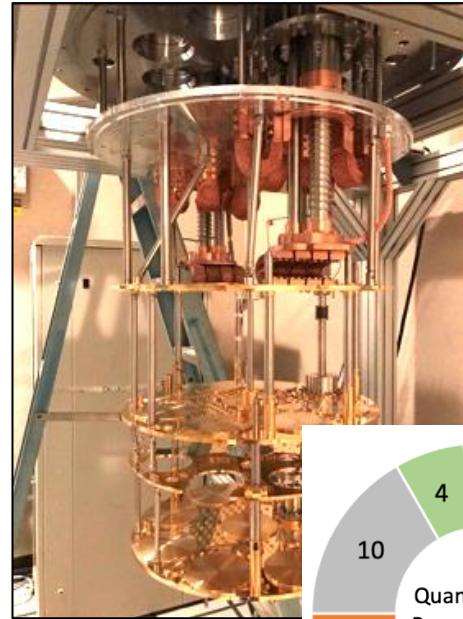
Advanced Manufacturing
Lab



Center for Micro- and
Nanotechnology

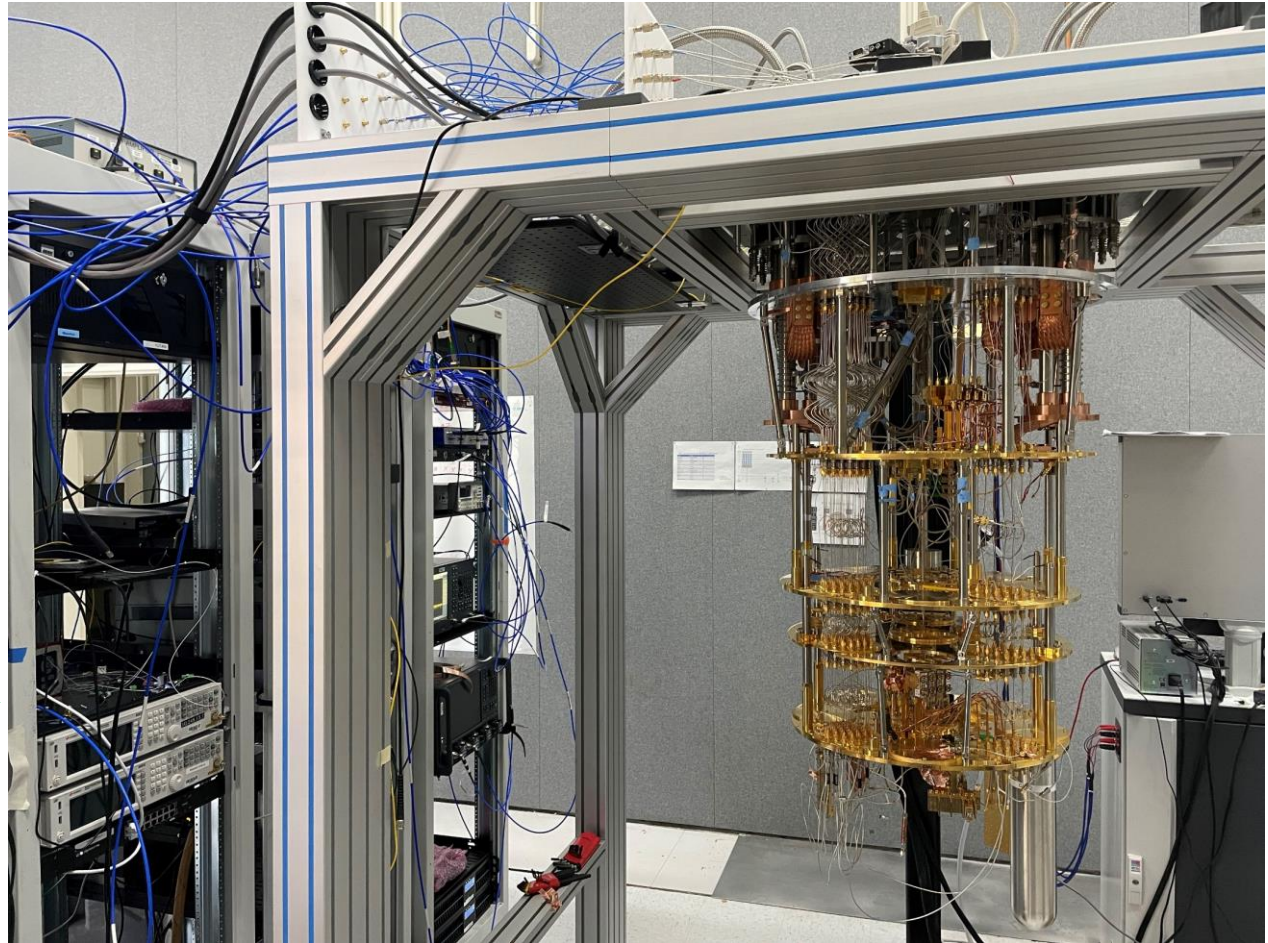
- Provides whitebox access to
 - Quantum processing platforms with state-of-the-art performance
 - Quantum device and materials characterization

- Supports ~15 teams and ~80 collaborators
 - DOE-SC, and NNSA sponsored projects including
 - NISQ Algorithm research and hardware codesign
 - Identification & amelioration of materials source of decoherence.
 - Quantum / classical control integration
 - Quantum optimal control and characterization



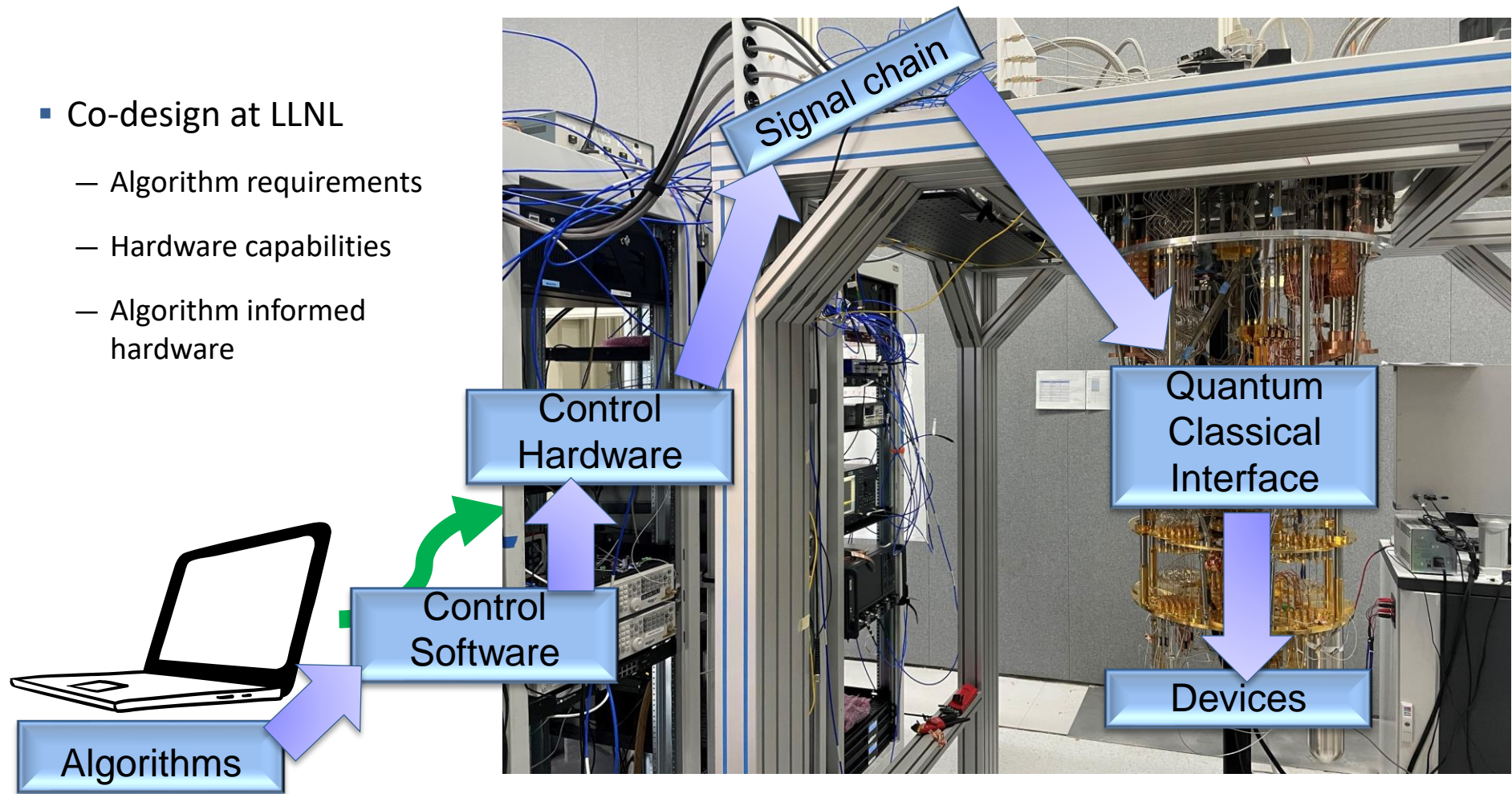
Measurement stack at LLNL

- Co-design at LLNL
 - Algorithm requirements
 - Hardware capabilities
 - Algorithm informed hardware



Measurement stack at LLNL

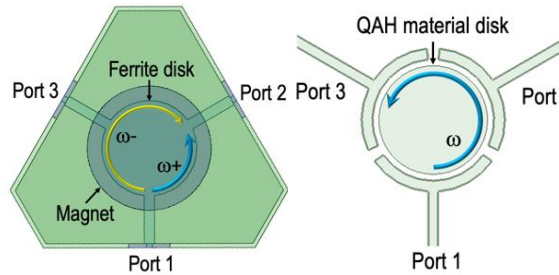
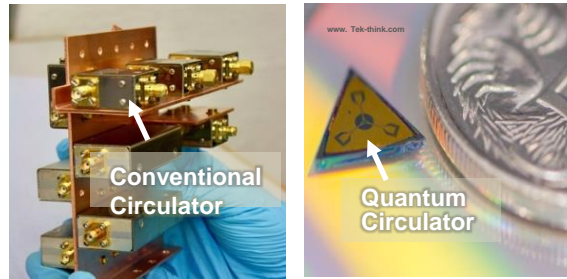
- Co-design at LLNL
 - Algorithm requirements
 - Hardware capabilities
 - Algorithm informed hardware



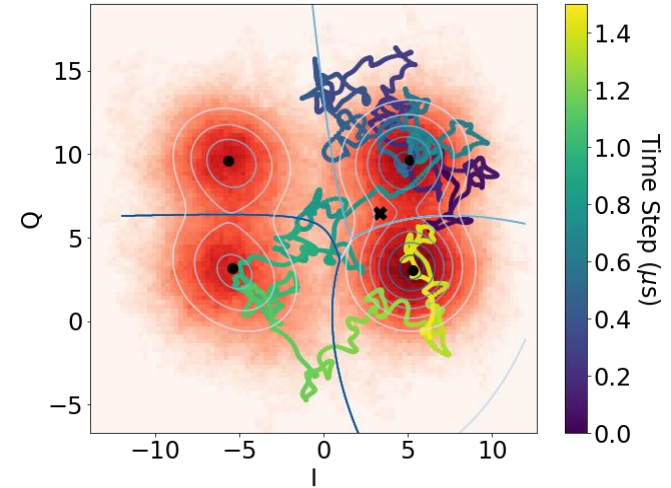
Hardware expertise for unique quantum application requirements

- On-chip topological-based non-reciprocal devices meet scalability requirements
- Increasing readout fidelity while decrease calibration time using Hidden Markov Models
- Developing RF photonic control interface
- Quantum sensing to enable large dynamic range computing gates

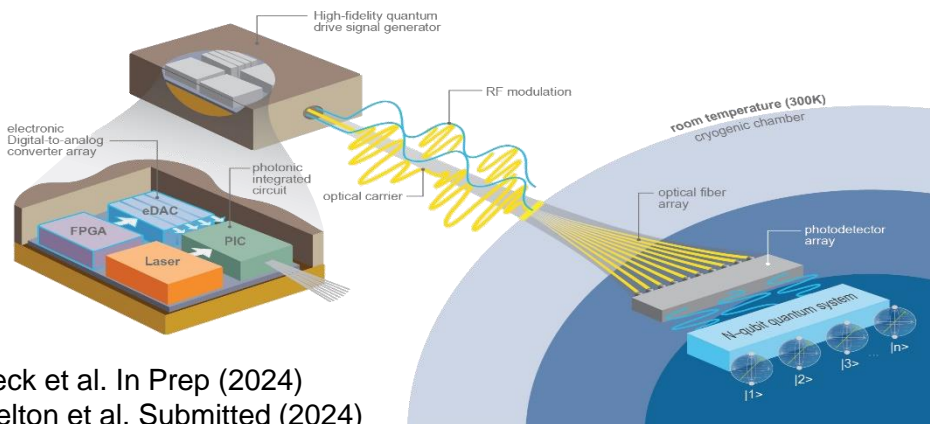
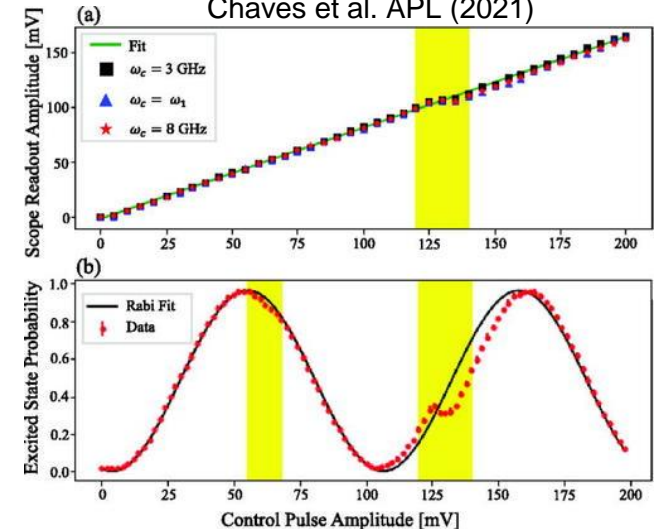
Martinez et al. PRR (2024)



Martinez et al. PRA (2020)



Chaves et al. APL (2021)



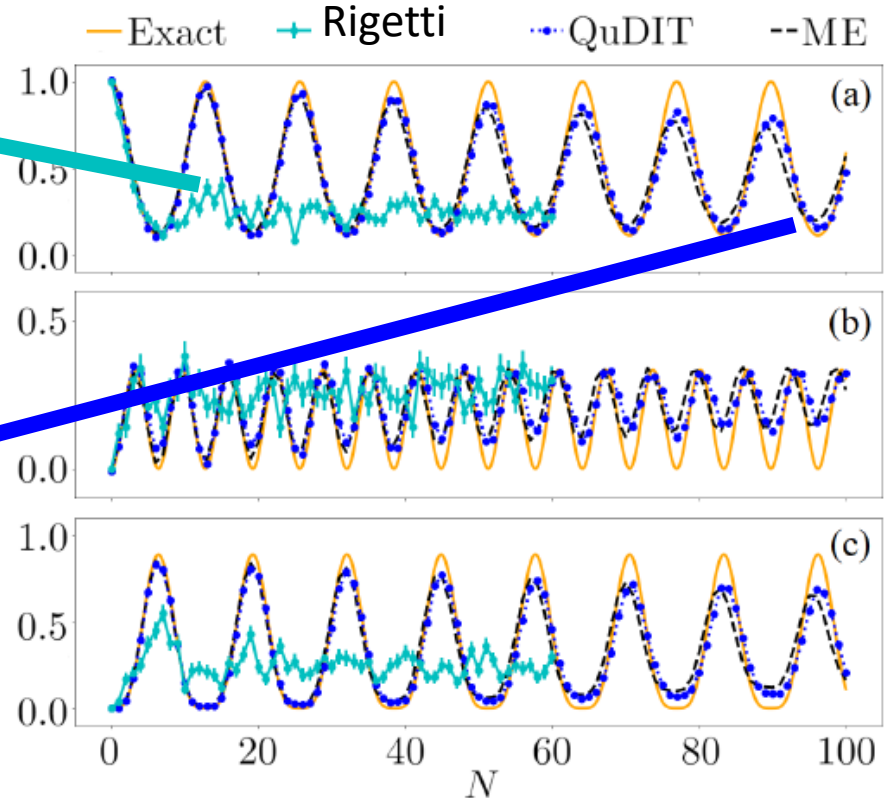
Beck et al. In Prep (2024)
Melton et al. Submitted (2024)

Algorithms
Control Software
Control Hardware
Signal chain
Quantum Classical Interface
Devices

Whitebox access is a minimum requirement for codesign

- Commercial setups
 - Gates designed for Universal quantum computation
 - Fully error corrected
 - Millions of qubits available
 - Not optimized for quantum simulation
- Conventional hardware installed in QuDIT with LLNL firmware
 - Optimized gates far superior to universal gate set.

Quantum computation of three-wave interactions with engineered cubic couplings



Shi et al. PRA (2021)

Algorithms

Control Software

Control Hardware

Signal chain

Quantum

Classical

Interface

Devices

Relaxation is due to two-level systems

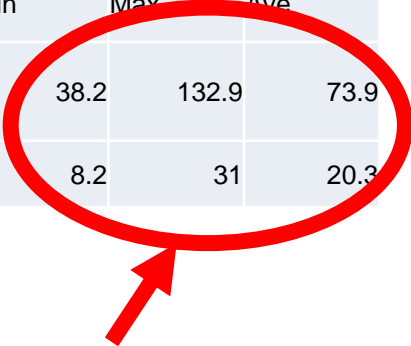
<https://quantumcomputingreport.com/scorecards/qubit-quality/>

Computer	Qubit Count	T1 (μ sec)		
		Min	Max	Ave
IBM Q System One	20	38.2	132.9	73.9
Rigetti 19Q Acorn	19	8.2	31	20.3

Relaxation is due to two-level systems

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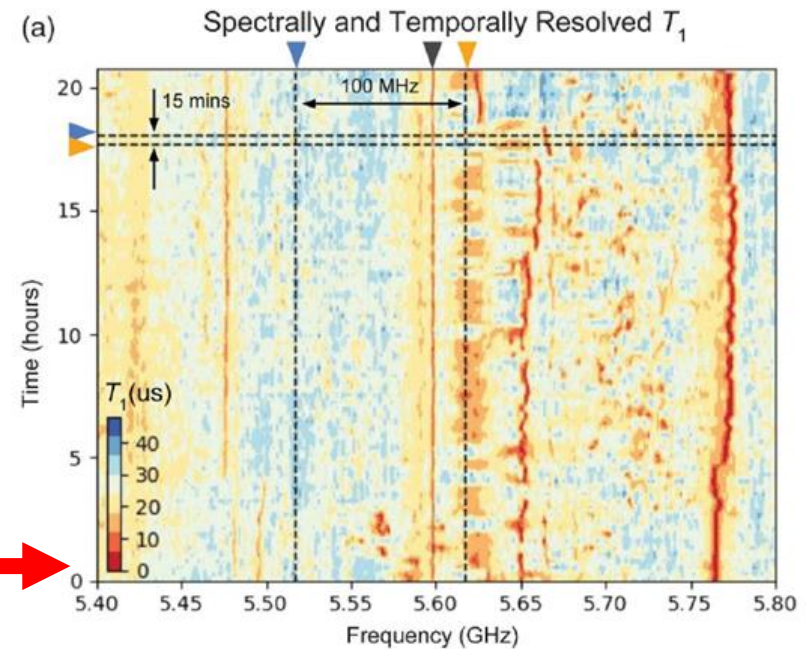
- Large scatter in relaxation times

Relaxation is due to two-level systems

<https://quantumcomputingreport.com/scorecards/qubit-quality/>

Computer	Qubit Count	T1 (μsec)		
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IBM Q System One	20	38.2	132.9	73.9
Rigetti 19Q Acorn	19	8.2	31	20.3

- Large scatter in relaxation times
- Defect drift over time
- Large unusable bandwidth



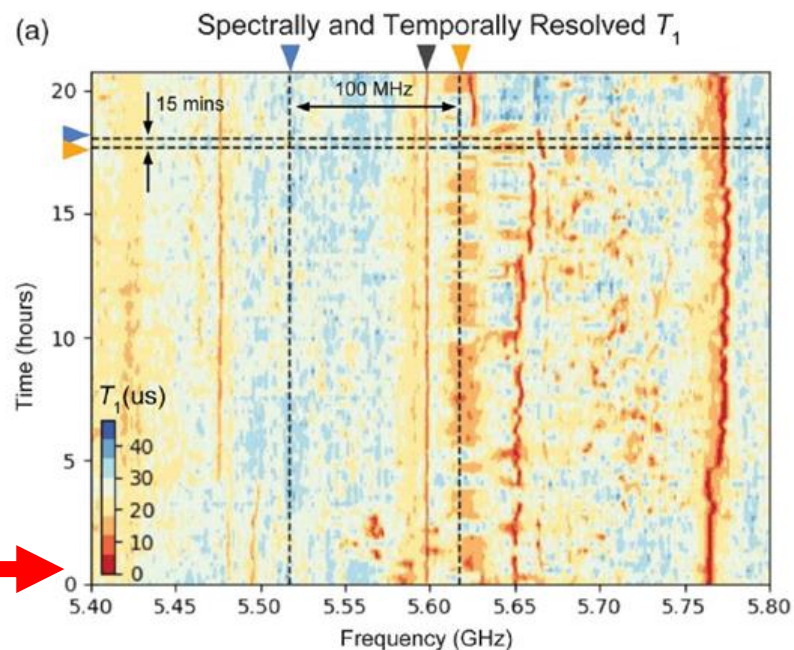
Google: PRL 121, 090502 (2018)

Relaxation is due to two-level systems

<https://quantumcomputingreport.com/scorecards/qubit-quality/>

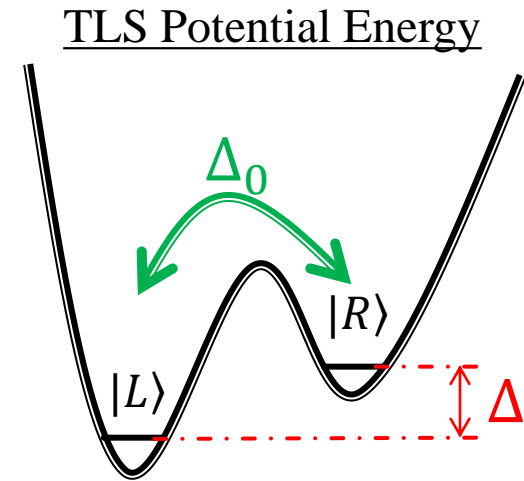
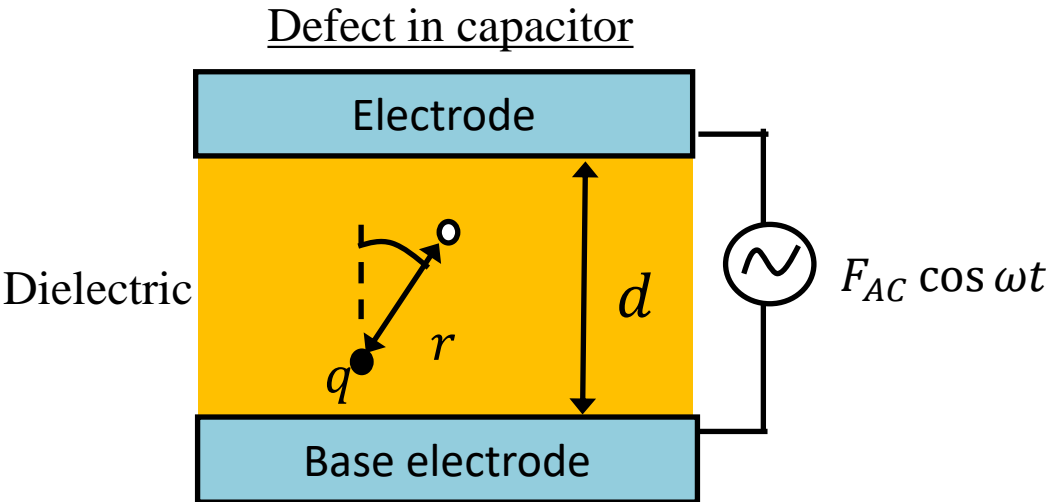
Computer	Qubit Count	T1 (μsec)		
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- Large scatter in relaxation times
- Defect drift over time
- Large unusable bandwidth
- Explained by standard tunneling system model?
 - Continuum of states
 - Unknown e-field coupling
 - Unknown strain-field coupling
 - Random fluctuations cause dropouts



Google: PRL 121, 090502 (2018)

The two-level system model



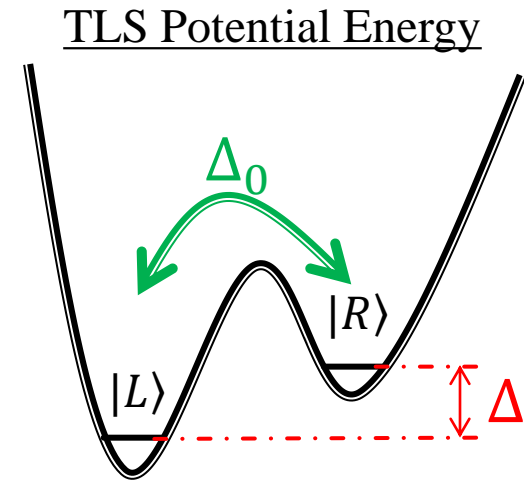
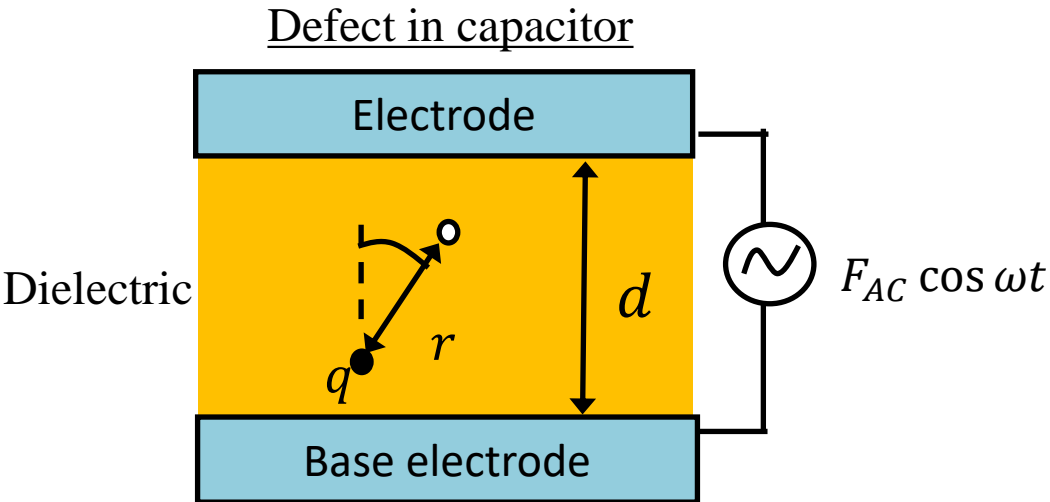
TLS Hamiltonian:

$$H = \frac{1}{2} \begin{bmatrix} \Delta & \Delta_0 \\ \Delta_0 & -\Delta \end{bmatrix}$$

$$\mathcal{E}_{TLS} = \sqrt{\Delta'^2 + \Delta_0^2}$$

W. A. Phillips, Reports on Progress in Physics 50, 1657 (1999)
 P. W. Anderson et. al, *Philosophical Magazine*, 25, 1 (1972)

The two-level system model



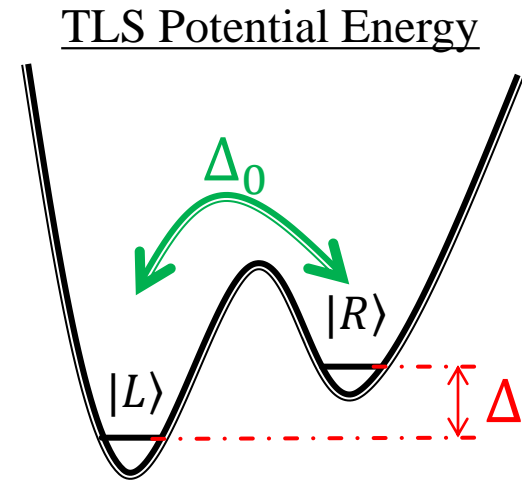
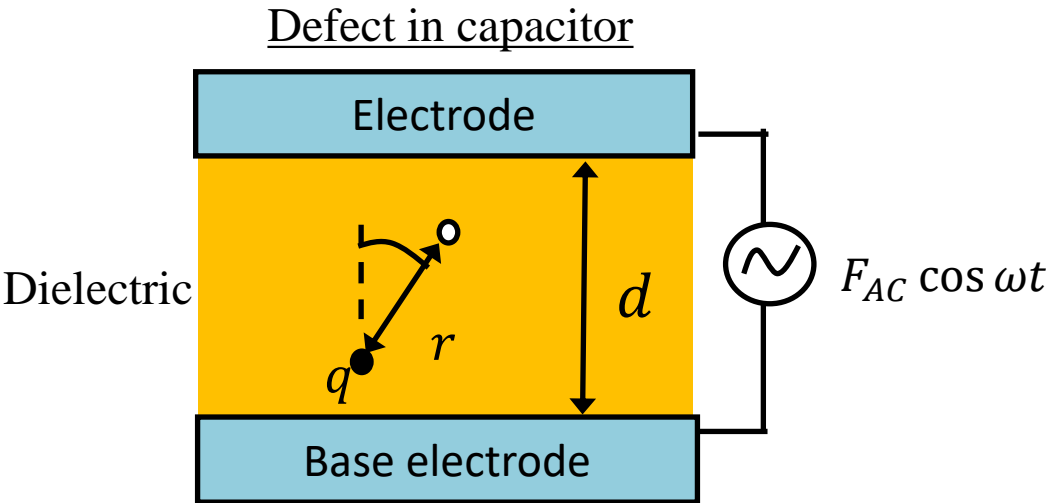
TLS Hamiltonian:

$$H = \frac{1}{2} \begin{bmatrix} \Delta & \Delta_0 \\ \Delta_0 & -\Delta \end{bmatrix} + H_{int} \quad \mathcal{E}_{TLS} = \sqrt{\Delta'^2 + \Delta_0^2}$$

$$H_{int} = \left| \frac{\Delta}{E} \sigma_z + \frac{\Delta_0}{E} \sigma_x \right| \vec{p} \cdot \vec{F} + \left| \frac{\Delta}{E} \sigma_z + \frac{\Delta_0}{E} \sigma_x \right| \gamma e$$

W. A. Phillips, Reports on Progress in Physics 50, 1657 (1999)
 P. W. Anderson et. al, *Philosophical Magazine*, 25, 1 (1972)

The two-level system model



TLS Hamiltonian:

$$H = \frac{1}{2} \begin{bmatrix} \Delta & \Delta_0 \\ \Delta_0 & -\Delta \end{bmatrix} \begin{array}{l} \text{Electric field} \\ \text{coupling} \end{array} LS = \sqrt{\quad} \begin{array}{l} \text{Strain field} \\ \text{coupling} \end{array}$$

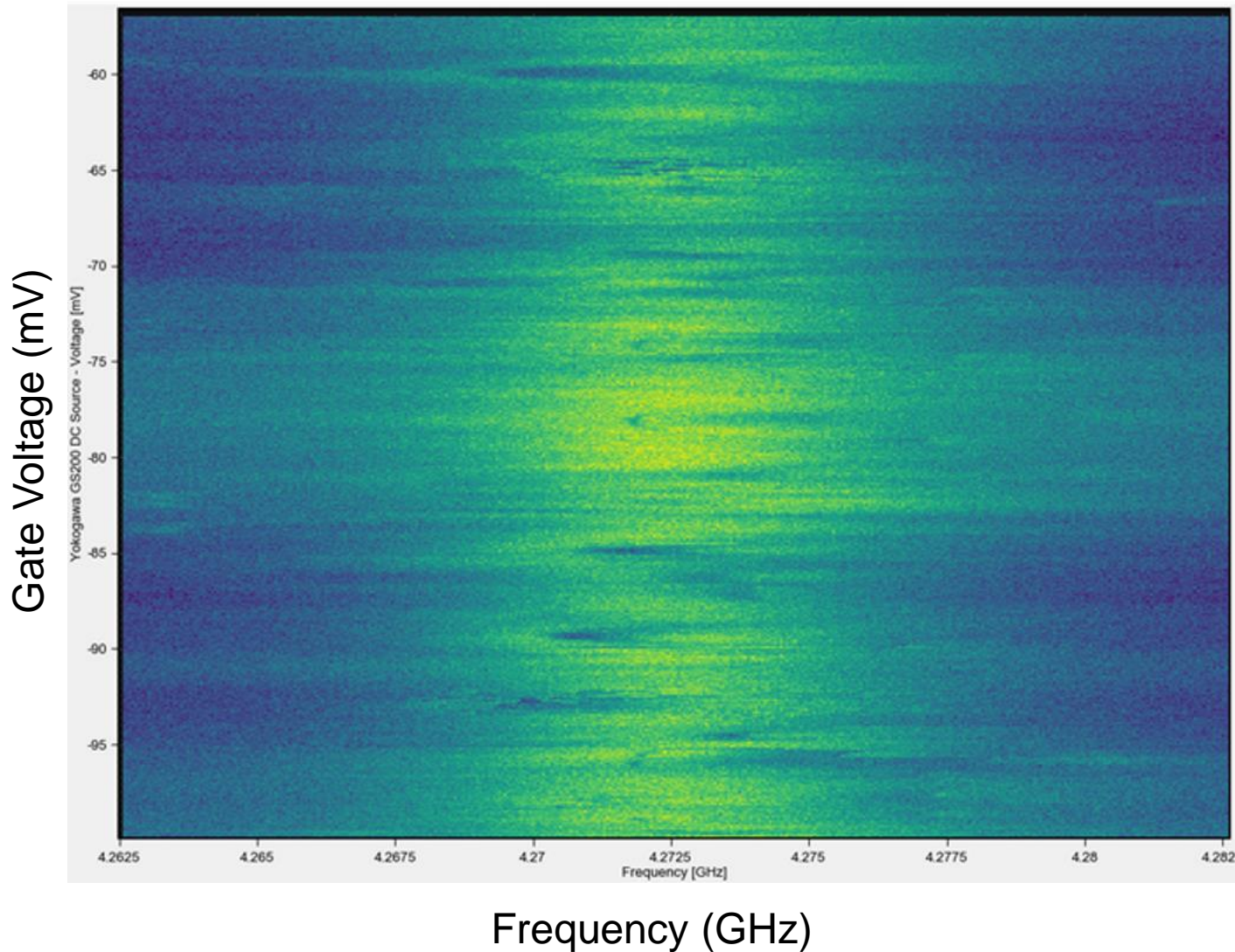
$$H_{int} = \left| \frac{\Delta}{E} \sigma_z + \frac{\Delta_0}{E} \sigma_x \right| \vec{p} \cdot \vec{F} + \left| \frac{\Delta}{E} \sigma_z + \frac{\Delta_0}{E} \sigma_x \right| \gamma e$$

T_1 relaxation:

- TLS excited by a qubit photon
- TLS relaxes by emitting a phonon.

W. A. Phillips, Reports on Progress in Physics 50, 1657 (1999)
 P. W. Anderson et. al, *Philosophical Magazine*, 25, 1 (1972)

Spectroscopically imaging TLS using low capacitor-volume resonators

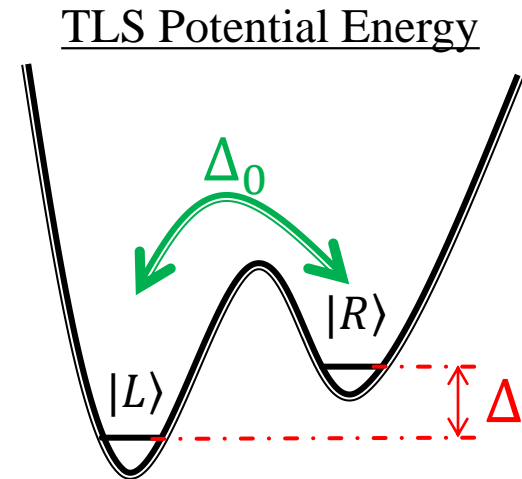
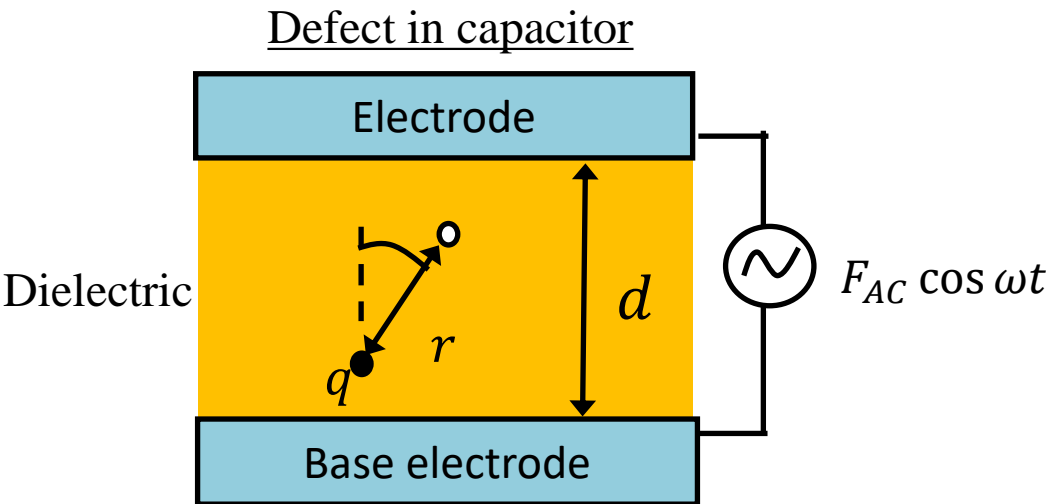


Colorbar:
 $|S_{21}|$ Transmission

$$\mathcal{E}_{TLS} = \sqrt{\Delta'^2 + \Delta_0^2}$$

$$\Delta' = \Delta + 2\vec{p} \cdot \vec{E}$$

The two-level system model



TLS Hamiltonian:

$$H = \frac{1}{2} \begin{bmatrix} \Delta & \Delta_0 \\ \Delta_0 & -\Delta \end{bmatrix} \begin{array}{l} \text{Electric field} \\ \text{coupling} \end{array} LS = \sqrt{\quad} \begin{array}{l} \text{Strain field} \\ \text{coupling} \end{array}$$

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T_1 relaxation:

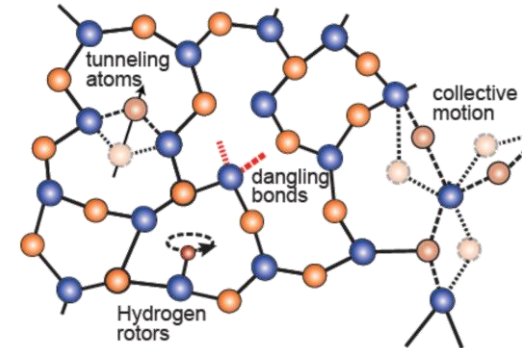
- TLS excited by a qubit photon
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W. A. Phillips, Reports on Progress in Physics 50, 1657 (1999)
 P. W. Anderson et. al, *Philosophical Magazine*, 25, 1 (1972)

TLS locations

Rep. Prog. Phys. **82**, 124501 (2019).

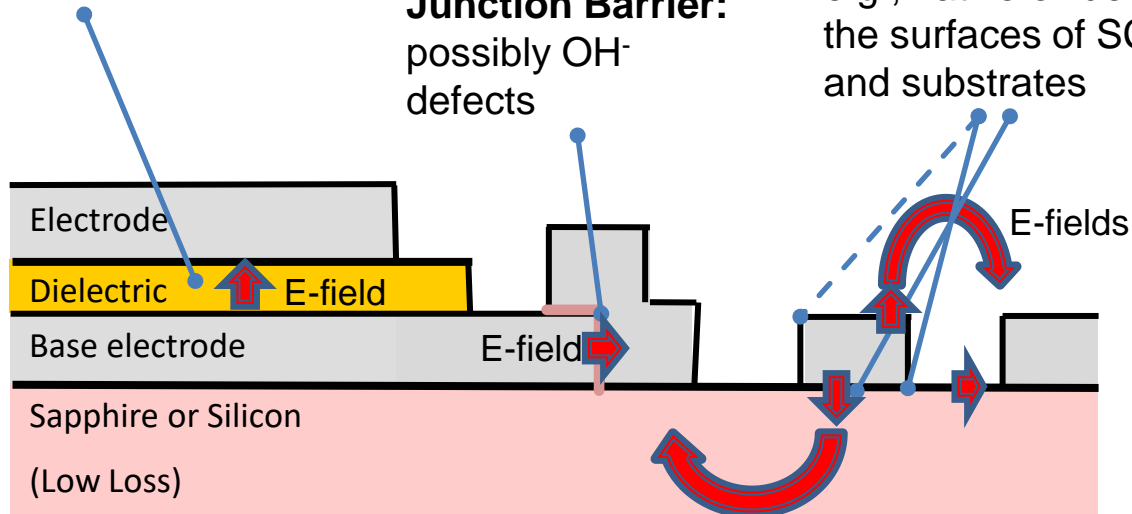
Chemical Residues And Particles Couple to E-Fields



Imperfect Dielectrics:
microstrips, capacitors,
and crossovers

**α -Al₂O₃
Josephson
Junction Barrier:**
possibly OH⁻
defects

Surface Oxides:
e.g., native oxide on
the surfaces of SCs
and substrates



TLS locations

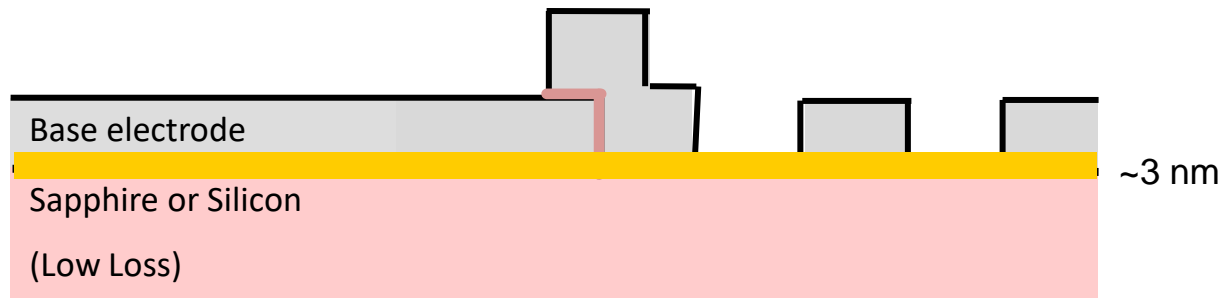
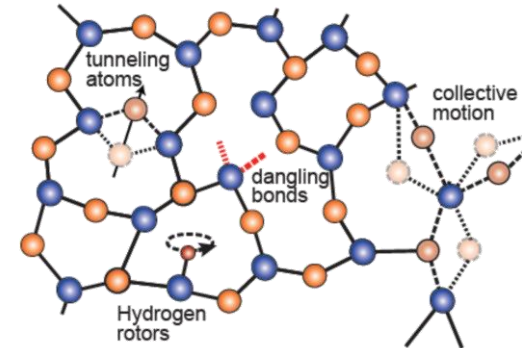
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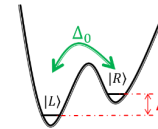
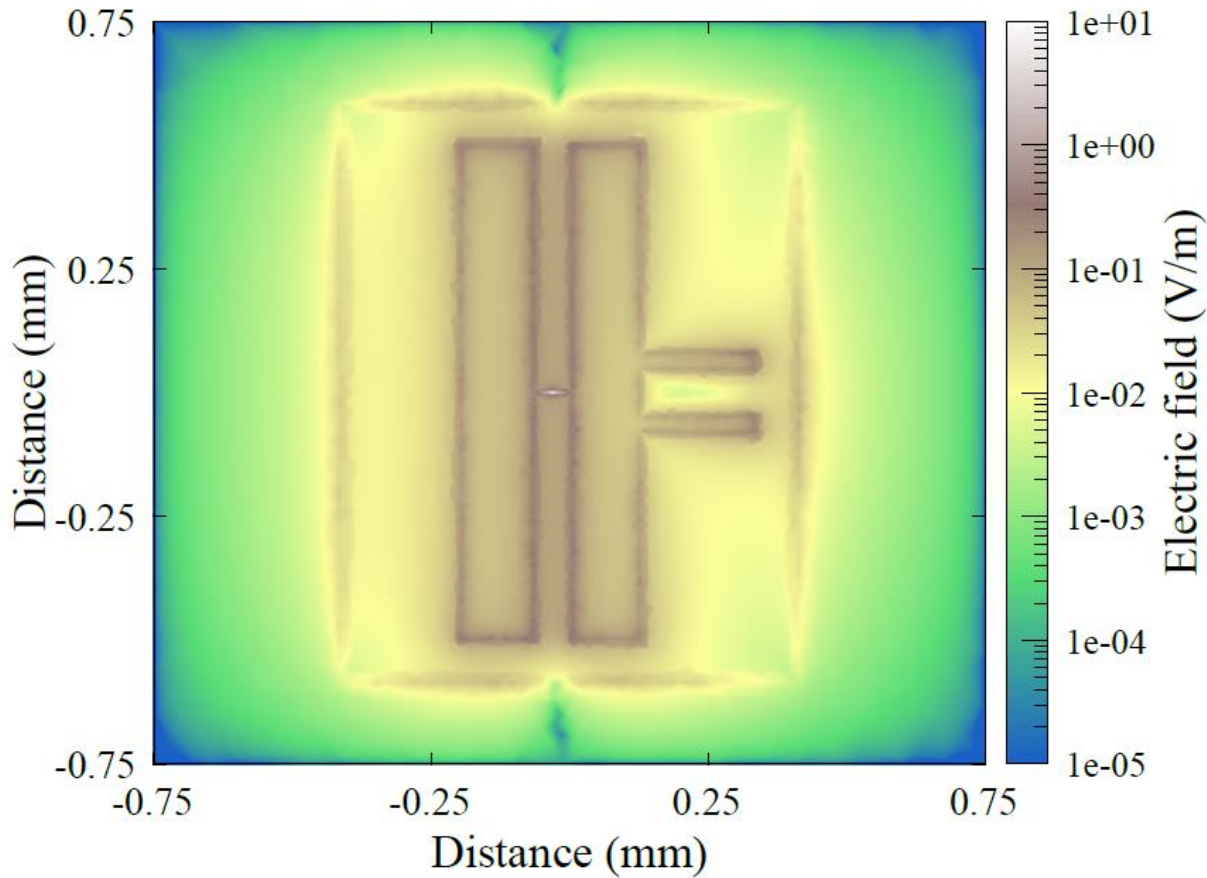
Surface Oxides:
e.g., native oxide on
the surfaces of SCs
and substrates

Rep. Prog. Phys. **82**, 124501 (2019).



Step 1: Model electric fields of a device

TLS $\sim 0.5/\mu\text{m}^2$



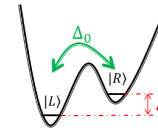
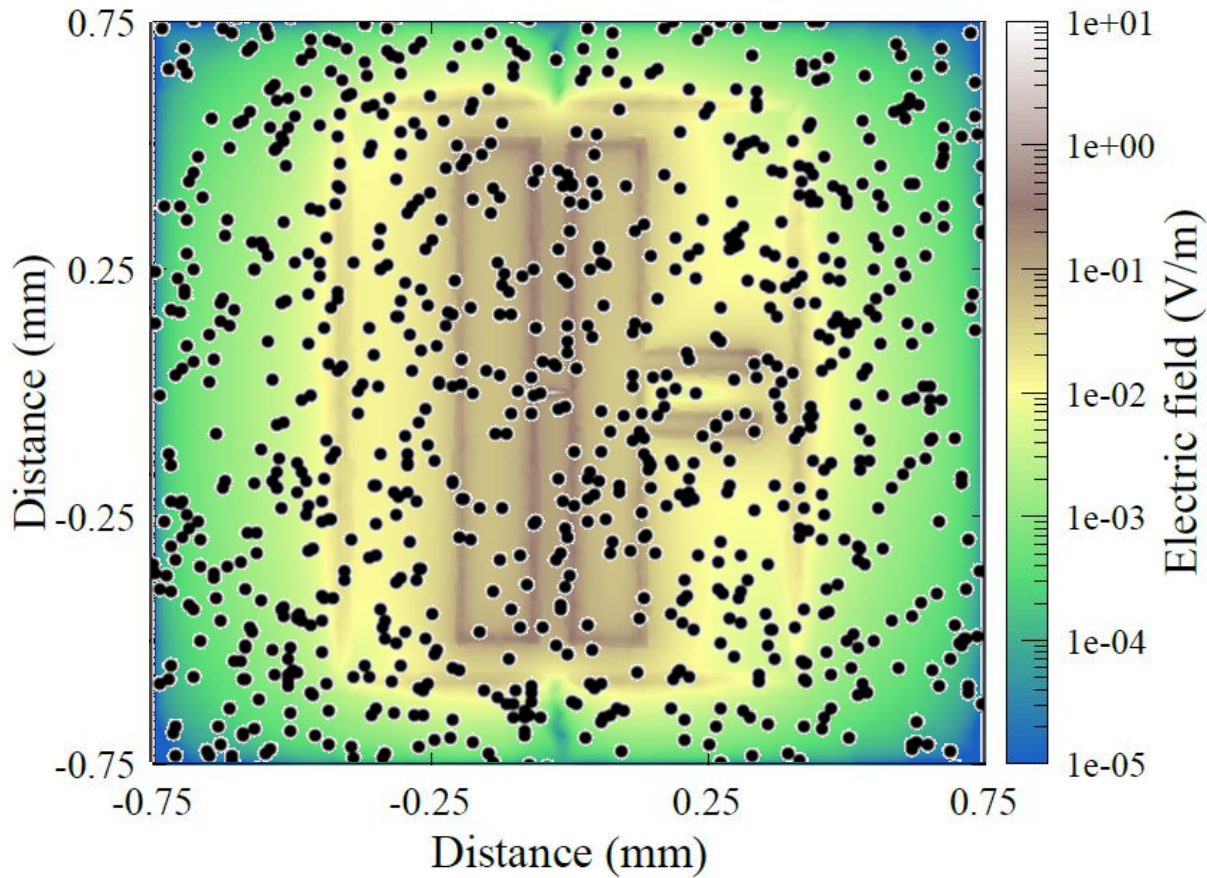
Coupling:

$$\Omega_i = \frac{\vec{p} \cdot \vec{E}_i}{\hbar} \frac{\Delta_0^i}{\text{Energy}}$$

arXiv:2211.08535

Step 2: Place one million TLS

TLS $\sim 0.5/\mu\text{m}^2$



Coupling:

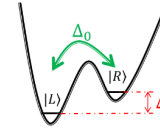
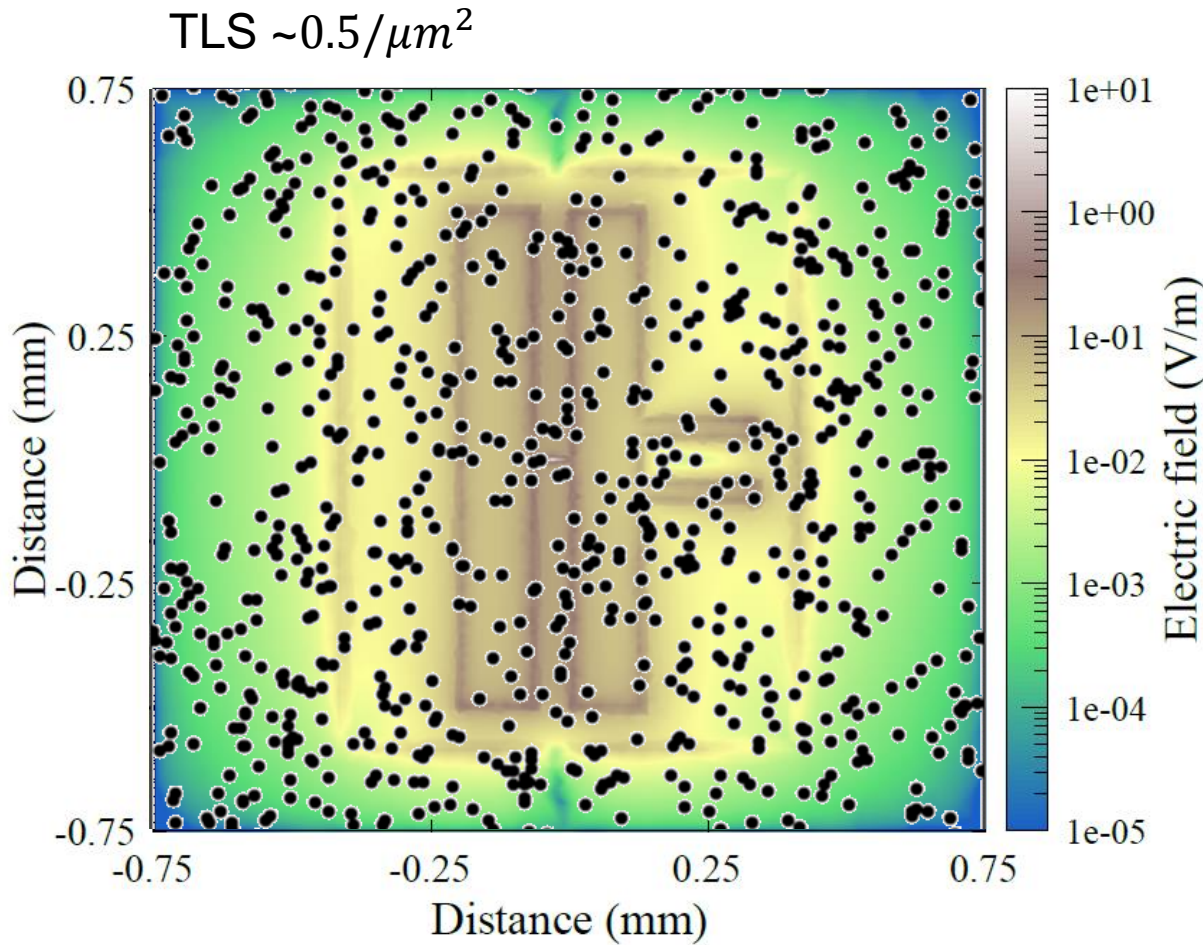
$$\Omega_i = \frac{\vec{p} \cdot \vec{E}_i}{\hbar} \frac{\Delta_0^i}{\text{Energy}}$$

Number of TLS

$$N = \int \int \frac{P_0 V}{\Delta_0} d\Delta_0 d\Delta$$

arXiv:2211.08535

Step 2: Place one million TLS -> select 200 with highest couple



Coupling:

$$\Omega_i = \frac{\vec{p} \cdot \vec{E}_i}{\hbar} \frac{\Delta_0^i}{\text{Energy}}$$

Number of TLS

$$N = \int \int \frac{P_0 V}{\Delta_0} d\Delta_0 d\Delta$$

$$= \int_d^{\pi/2} \int_{\hbar\omega-\delta}^{\hbar\omega+\delta} \frac{P_0 V}{\sin \theta} dE d\theta$$

$$P_0 = 10^{44} / \text{Jm}^3$$

$$V = 3 \text{ nm} \times (1.5 \text{ mm})^2$$

$$\min\left(\frac{\Delta_0}{E}\right) \cong d \cong 10^{-50}$$

$$\delta = \hbar \times 10 \text{ MHz}$$

$$\omega = 2\pi \times 5 \text{ GHz}$$

arXiv:2211.08535

Step 3: Simulate 200 TLS using full Lindblad

Full Lindblad Simulation

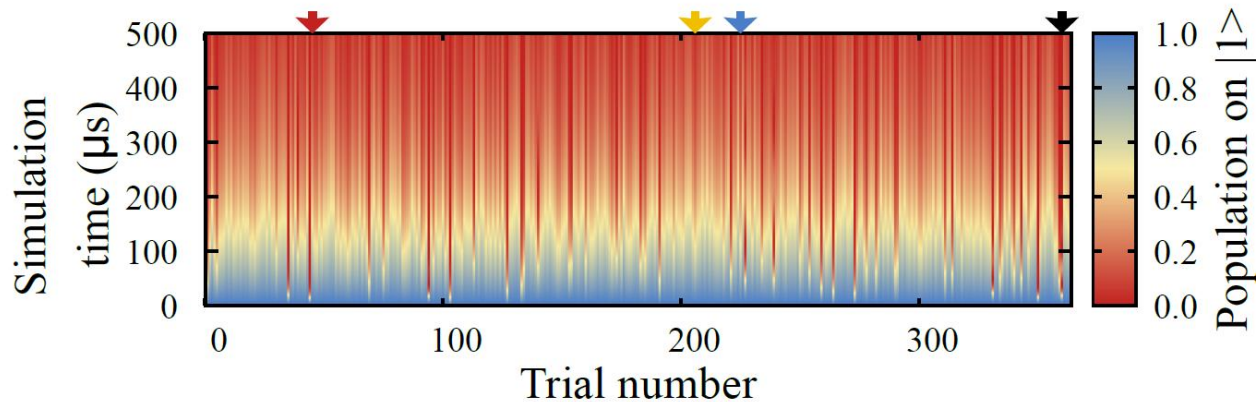
- Discard Hilbert space with > 1 photon
 - initialized qubit with 1 photon
 - Only include loss due to TLS-phonon coupling
- Simulation uses 200 TLSs
 - $\Omega_{TLSi} = \frac{\vec{p} \cdot \vec{F}_i}{\hbar} \frac{\Delta_0^i}{\hbar \omega}$, where $|\vec{p}|$ is adjustable
 - $T_{1,TLSi} = \frac{T_{1,min}}{(\Delta_0^i)^2}$, where $T_{1,min}$ is adjustable

$$\hat{H} = \hbar \begin{matrix} & |g\rangle & |q\rangle & |TLS1\rangle & |TLS2\rangle & \dots & |TLSN\rangle \\ \begin{pmatrix} 0 & 0 & 0 & 0 & \dots & 0 \\ 0 & \omega_q & \Omega_{TLS1} & \Omega_{TLS2} & \dots & \Omega_{TLSN} \\ 0 & \Omega_{TLS1} & \omega_{TLS1} & 0 & \dots & 0 \\ 0 & \Omega_{TLS2} & 0 & \omega_{TLS2} & \dots & 0 \\ \vdots & \vdots & \vdots & \vdots & \ddots & \vdots \\ 0 & \Omega_{TLSN} & 0 & 0 & \dots & \omega_{TLSN} \end{pmatrix} \end{matrix}$$

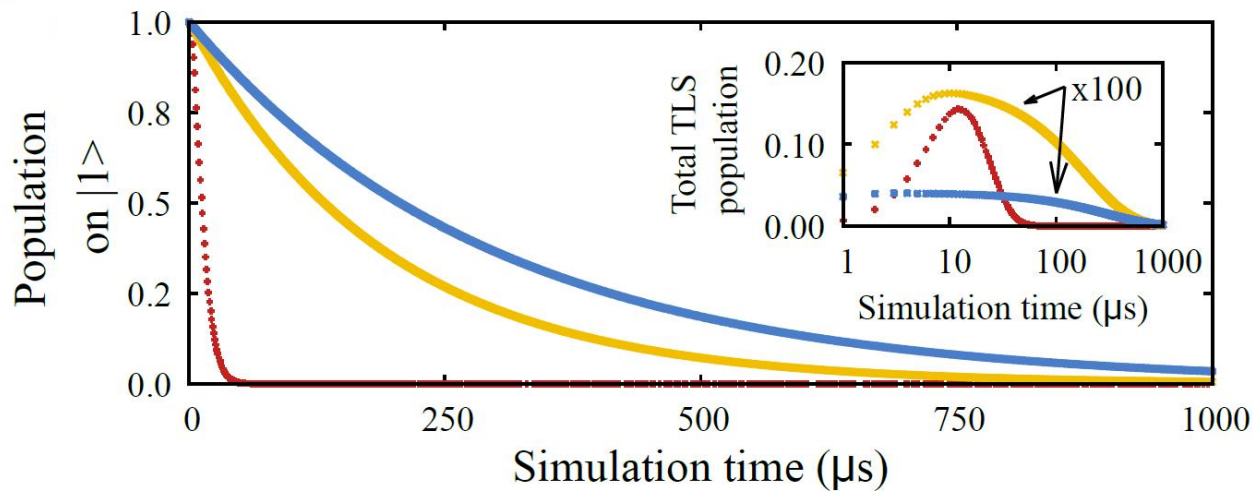
$$L_i = \begin{pmatrix} 0 & 0 & \dots & 1/\sqrt{T_{1,TLSi}} & \dots & 0 \\ 0 & 0 & \dots & 0 & \dots & 0 \\ 0 & 0 & \dots & 0 & \dots & 0 \\ 0 & 0 & \dots & 0 & \dots & 0 \\ \vdots & \vdots & \ddots & \vdots & \ddots & \vdots \\ 0 & 0 & \dots & 0 & \dots & 0 \end{pmatrix}$$

arXiv:2211.08535

High T_1 with occasional dropouts for different TLS configurations

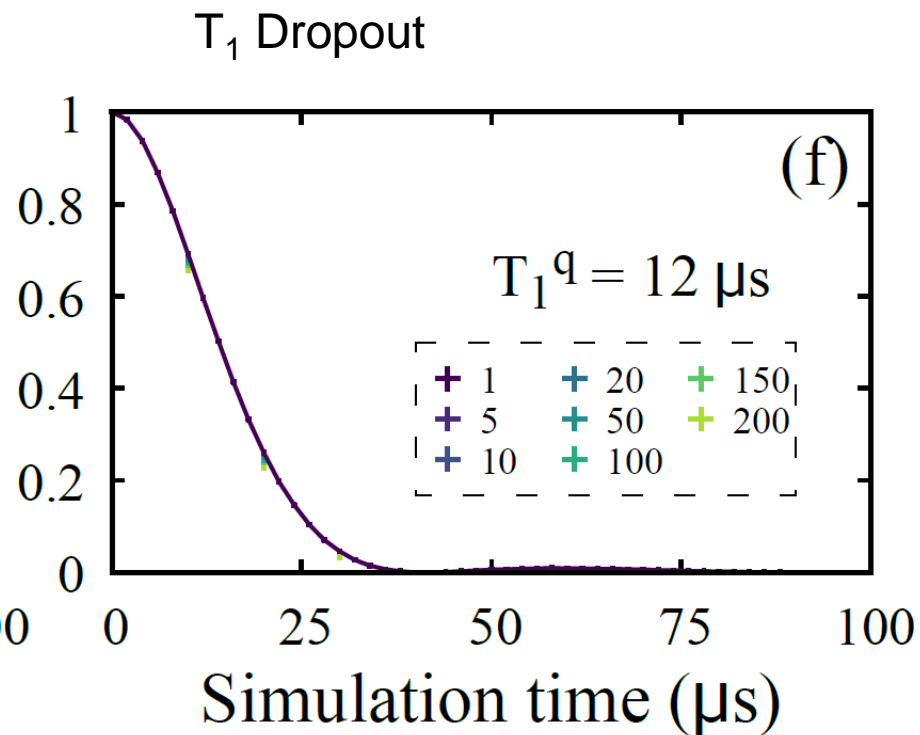
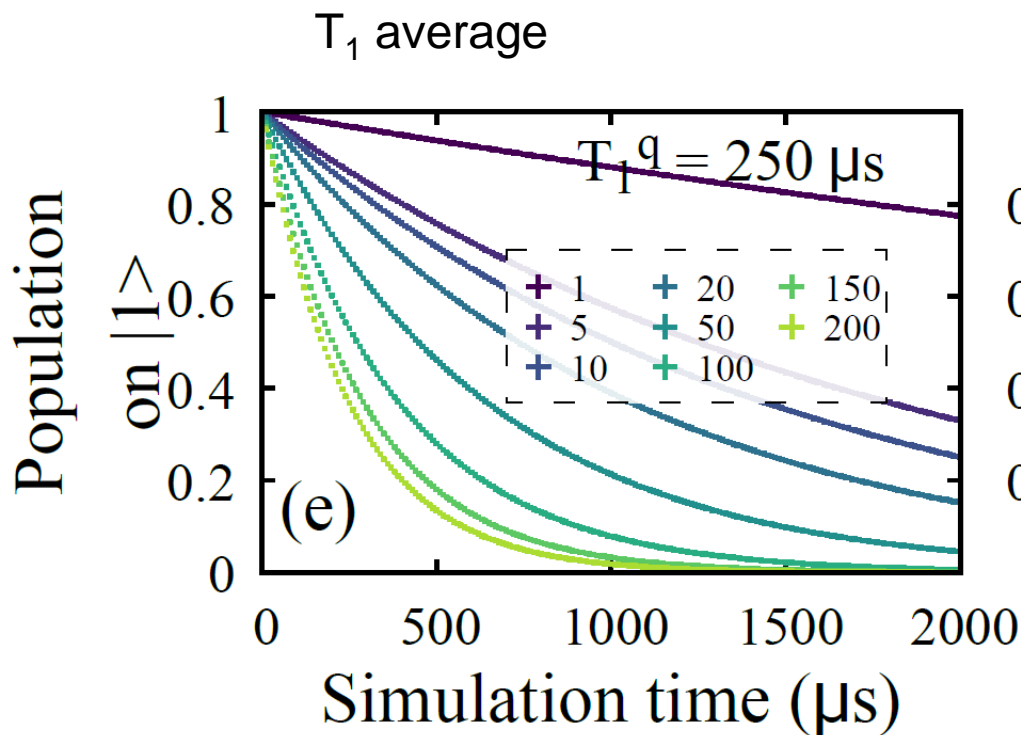


- $T_1 = 6 \mu\text{s}$
- $T_1 = 190 \mu\text{s}$
- $T_1 = 297 \mu\text{s}$



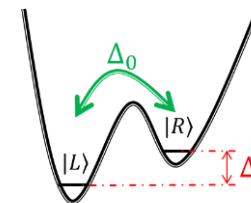
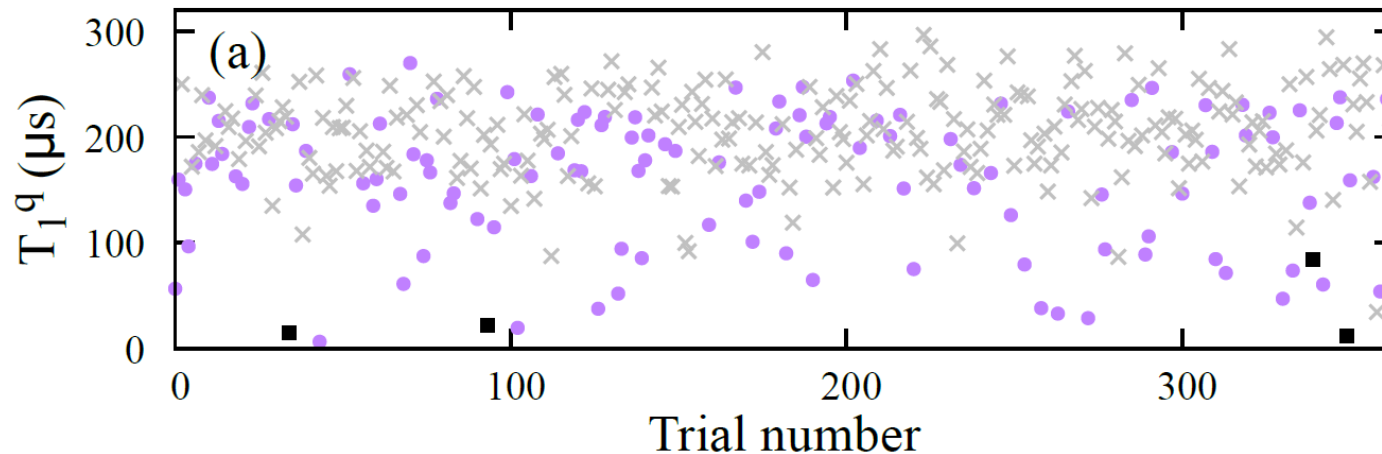
arXiv:2211.08535

Qubit dynamics dominated by between 1 and 150 TLS



arXiv:2211.08535

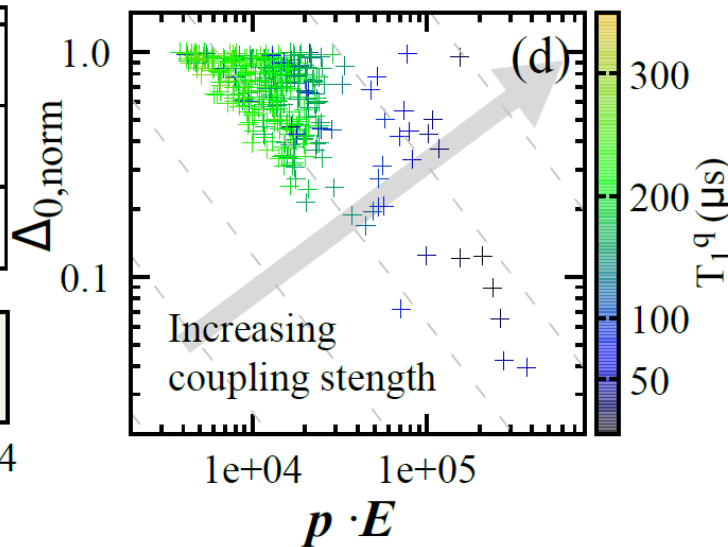
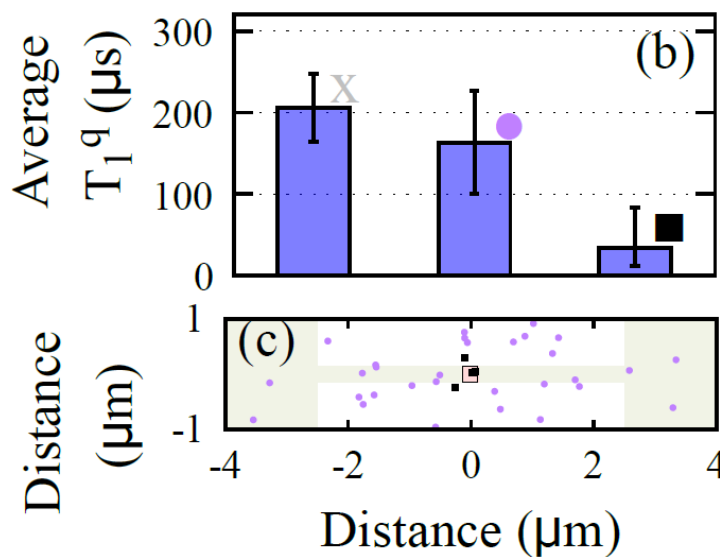
Dropouts dominated by high E-field, *not* coupling strength



Coupling:

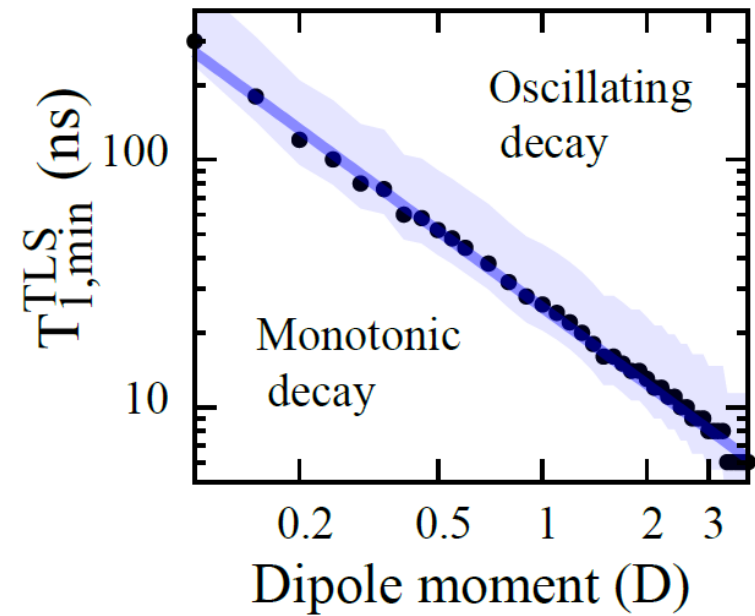
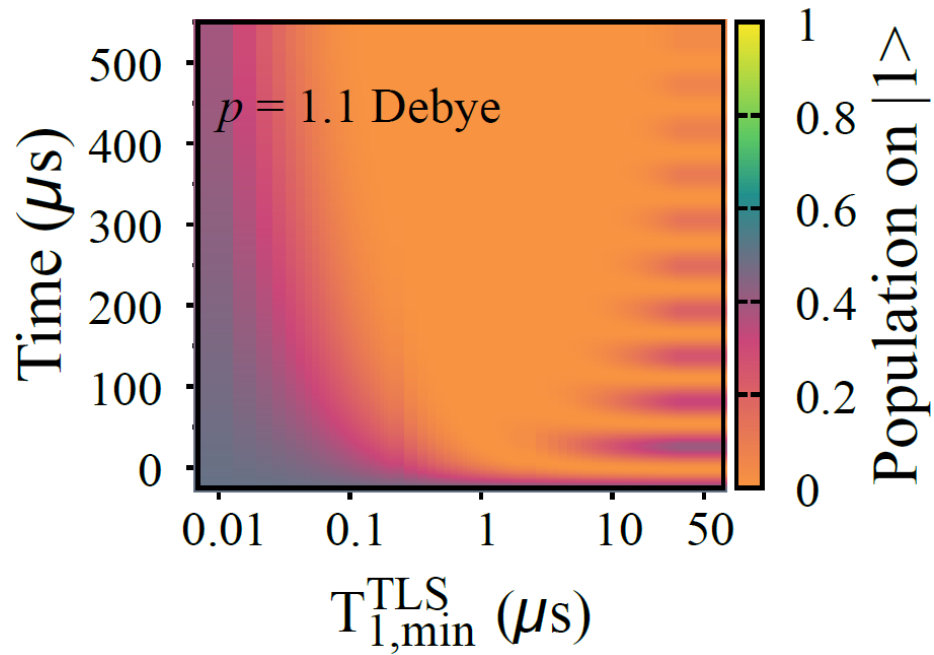
$$\Omega_i = \frac{\vec{p} \cdot \vec{E}_i}{\hbar} \frac{\Delta_0^i}{\text{Energy}}$$

$$T_1^{TLS} \propto \frac{1}{\Delta_0^2}$$

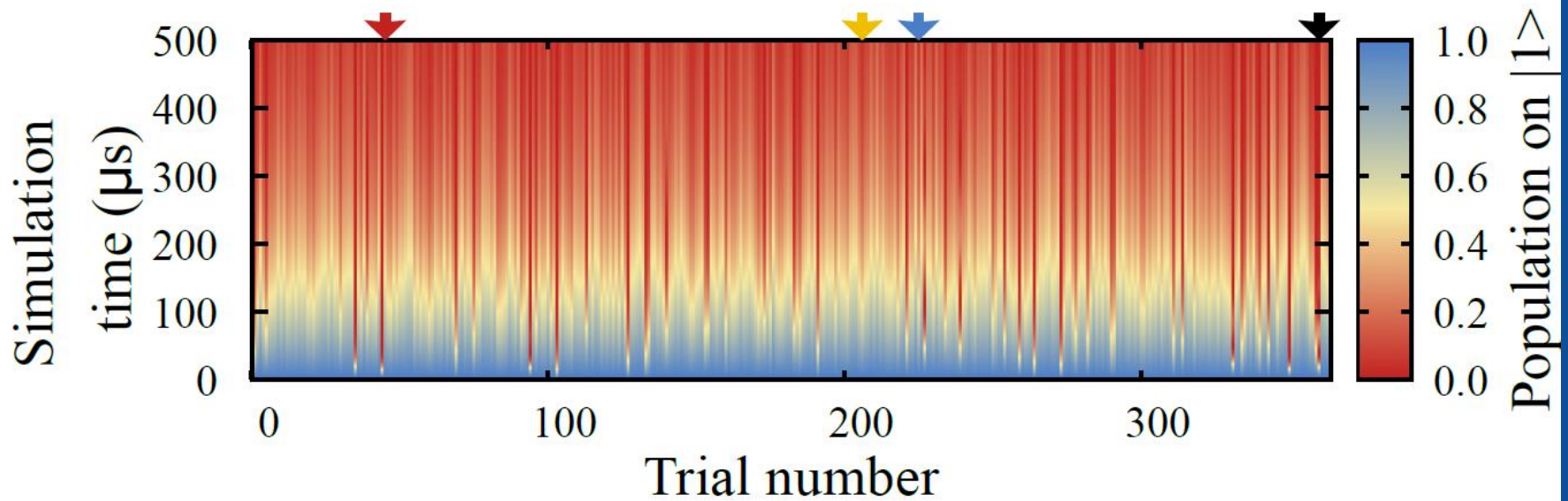


arXiv:2211.08535

We place limits on TLS T_1 times depending on Dipole moment



arXiv:2211.08535



Simulating the standard TLS model:

- Reproduced T_1 dropouts
- Dropout indicator is E-Field, not coupling strength
- Put bounds on dipole moment and $T_{1,\min}$

Supplemental

